



### **60V N-CHANNEL ENHANCEMENT MODE MOSFET** PowerDI5060-8

### **Product Summary**

| BV <sub>DSS</sub> | Rds(on)                         | I <sub>D</sub><br>T <sub>C</sub> = +25°C |
|-------------------|---------------------------------|--|
| 60V               | 7.9mΩ @ V <sub>GS</sub> = 10V   | 69.2A                                    |
| 00 V              | 10.8mΩ @ V <sub>GS</sub> = 4.5V | 59.2A                                    |

### **Features and Benefits**

- 100% Unclamped Inductive Switching (UIS) Test in Production -Ensures More Reliable and Robust End Application
- High Conversion Efficiency
- Low RDS(ON)—Minimizes On-State Losses
- Low Input Capacitance
- Fast Switching Speed
- **ESD Protected Gate**
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/104/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please contact us or your local Diodes representative.

https://www.diodes.com/quality/product-definitions/

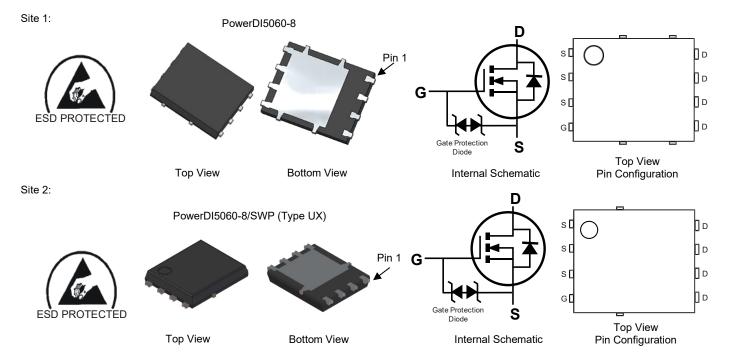
# **Description and Applications**

This MOSFET is designed to minimize the on-state resistance (RDS(ON)) yet maintain superior switching performance, making it ideal for high-efficiency power-management applications.

- Synchronous rectifiers
- DC-DC converters
- Power management

### **Mechanical Data**

- Package: PowerDI®5060-8
- Package Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish—Matte Tin Annealed over Copper Leadframe; Solderable per MIL-STD-202, Method 208 @3
- Weight: 0.097 grams (Approximate)



Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

PowerDI is a registered trademark of Diodes Incorporated in the United States and other countries.



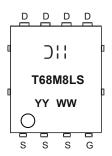
# Ordering Information (Note 4)

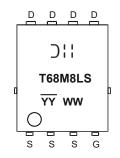
| Orderable Part Number | Dockogo                     | Packing |             |  |
|-----------------------|-----------------------------|---------|-------------|--|
| Orderable Part Number | Package                     | Qty.    | Carrier     |  |
| DMT68M8LPS-13         | PowerDI5060-8               | 2500    | Tape & Reel |  |
| DMT68M8LPS-13         | PowerDI5060-8/SWP (Type UX) | 2500    | Tape & Reel |  |

Note:

4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

# **Marking Information**





T68M8LS = Product Type Marking Code
YYWW or YYWW = Date Code Marking
YY or YY = Last Two Digits of Year (ex: 25 = 2025)
WW = Week Code (01 to 53)

# **Maximum Ratings** (@TA = +25°C, unless otherwise specified.)

| Characteristic  | Symbol   | Value            | Unit         |    |
|---|--|------------------|--------------|----|
| Drain-Source Voltage  |  | VDSS             | 60           | V  |
| Gate-Source Voltage   |  | V <sub>GSS</sub> | ±20          | V  |
| Continuous Drain Current (Note 5) V <sub>GS</sub> = 10V         | T <sub>A</sub> = +25°C<br>T <sub>A</sub> = +70°C | I <sub>D</sub>   | 14.1<br>11.2 | Α  |
| Continuous Drain Current (Note 6) V <sub>GS</sub> = 10V         | T <sub>C</sub> = +25°C<br>T <sub>C</sub> = +70°C | lo               | 69.2<br>55.4 | Α  |
| Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)              | I <sub>DM</sub>                                  | 270              | Α            |    |
| Maximum Continuous Body Diode Forward Current (Note 6)          |  | Is               | 69           | Α  |
| Pulsed Body Diode Forward Current (10µs Pulse, Duty Cycle = 1%) |  | Іѕм              | 270          | Α  |
| Avalanche Current, L = 0.1mH                                    |  | las              | 28.1         | Α  |
| Avalanche Energy, L = 0.1mH                                     |  | Eas              | 39.5         | mJ |

## **Thermal Characteristics**

| Characteristic                                   |                        | Symbol            | Value       | Unit |
|--|------------------------|-------------------|-------------|------|
| Total Power Dissipation (Note 5)                 | T <sub>A</sub> = +25°C | PD                | 2.4         | W    |
| Thermal Resistance, Junction to Ambient (Note 5) |                        | Reja              | 53          | °C/W |
| Total Power Dissipation (Note 6)                 | T <sub>C</sub> = +25°C | P <sub>D</sub>    | 56.8        | W    |
| Thermal Resistance, Junction to Case (Note 6)    |                        | R <sub>0</sub> JC | 2.2         | °C/W |
| Operating and Storage Temperature Range          |                        | TJ, TSTG          | -55 to +150 | °C   |

Notes: 5. Device mounted on FR-4 substrate PCB, 2oz copper, with 1inch square copper plate.

6. Thermal resistance from junction to soldering point (on the exposed drain pad).



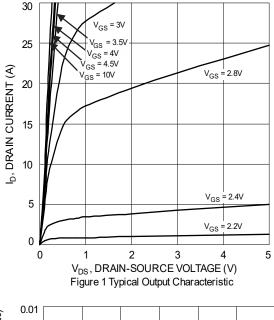
# Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

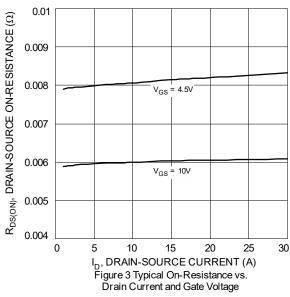
| Characteristic                             | Symbol                           | Min | Тур  | Max  | Unit  | Test Condition   |  |
|--|----------------------------------|-----|------|------|-------|--|--|
| OFF CHARACTERISTICS (Note 7)               |                                  |     |      |      |       |  |  |
| Drain-Source Breakdown Voltage             | BVDSS                            | 60  | _    | _    | V     | V <sub>GS</sub> = 0V, I <sub>D</sub> = 1mA                     |  |
| Zero Gate Voltage Drain Current            | IDSS                             | _   | -    | 1    | μA    | V <sub>DS</sub> = 48V, V <sub>GS</sub> = 0V                    |  |
| Gate-Source Leakage                        | Igss                             | _   | -    | ±10  | μA    | V <sub>GS</sub> = ±20V, V <sub>DS</sub> = 0V                   |  |
| ON CHARACTERISTICS (Note 7)                |                                  |     |      |      |       |  |  |
| Gate Threshold Voltage                     | V <sub>G</sub> S(TH)             | 1   | _    | 3    | V     | V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250μA     |  |
| Static Drain-Source On-Resistance          | D                                | _   | 5.9  | 7.9  | mΩ    | V <sub>GS</sub> = 10V, I <sub>D</sub> = 20A                    |  |
| Static Drain-Source On-Resistance          | R <sub>DS(ON)</sub>              | _   | 7.8  | 10.8 | 11122 | V <sub>GS</sub> = 4.5V, I <sub>D</sub> = 20A                   |  |
| Diode Forward Voltage                      | VsD                              | _   | 0.7  | 1.2  | V     | V <sub>GS</sub> = 0V, I <sub>S</sub> = 1A                      |  |
| DYNAMIC CHARACTERISTICS (Note 8)           | DYNAMIC CHARACTERISTICS (Note 8) |     |      |      |       |  |  |
| Input Capacitance                          | Ciss                             | _   | 2078 | _    |       | V <sub>DS</sub> = 30V, V <sub>GS</sub> = 0V,<br>f = 1MHz       |  |
| Output Capacitance                         | Coss                             | _   | 605  | _    | pF    |  |  |
| Reverse Transfer Capacitance               | Crss                             | _   | 44   | _    |       |  |  |
| Gate Resistance                            | Rg                               | _   | 1.71 | _    | Ω     | V <sub>DS</sub> = 0V, V <sub>GS</sub> = 0V, f = 1MHz           |  |
| Total Gate Charge (V <sub>GS</sub> = 4.5V) | Qg                               | _   | 14.4 | _    |       |  |  |
| Total Gate Charge (V <sub>GS</sub> = 10V)  | Qg                               | _   | 30   | _    | nC    | V <sub>DS</sub> = 30V, I <sub>D</sub> = 20A                    |  |
| Gate-Source Charge                         | Qgs                              | _   | 4.1  | _    | IIC   |  |  |
| Gate-Drain Charge                          | $Q_{gd}$                         | _   | 6.7  | _    |       |  |  |
| Turn-On Delay Time                         | t <sub>D</sub> (ON)              | _   | 5.2  | _    | ns    | $V_{DS} = 30V, V_{GS} = 10V,$ $I_{D} = 20A, R_{G} = 3.3\Omega$ |  |
| Turn-On Rise Time                          | t <sub>R</sub>                   | _   | 9.6  | _    |       |  |  |
| Turn-Off Delay Time                        | tD(OFF)                          | _   | 20.5 | _    |       |  |  |
| Turn-Off Fall Time                         | t <sub>F</sub>                   | _   | 8.9  | _    |       |  |  |
| Reverse-Recovery Time                      | t <sub>RR</sub>                  | _   | 32.5 | _    | ns    |  |  |
| Reverse-Recovery Charge                    | Qrr                              | _   | 22.8 | _    | nC    | F = 20A, di/dt = 100A/μs                                       |  |

Notes:

<sup>7.</sup> Short duration pulse test used to minimize self-heating effect. 8. Guaranteed by design. Not subject to product testing.







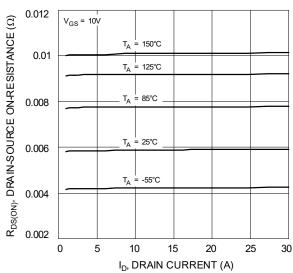
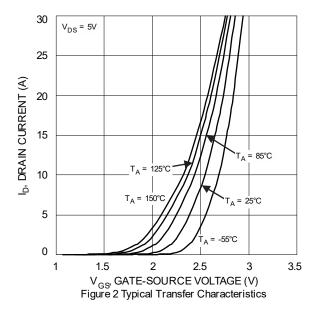


Figure 5 Typical On-Resistance vs. Drain Current and Temperature



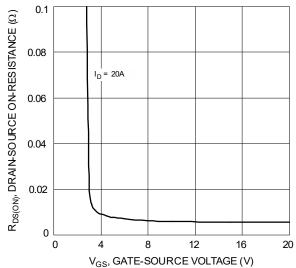


Figure 4 Typical Drain-Source On-Resistance vs. Gate-Source Voltage

1.8  $V_{GS}$ R<sub>DS(ON)</sub>, DRAIN-SOURCE ON-RESISTANCE (NORMALIZED) 1.6 V<sub>GS</sub> = 4.5V I<sub>D</sub> = 20A 1.2 1 8.0 0.6

50 T<sub>J</sub>, JUNCTION TEMPERATURE (°C) Figure 6 On-Resistance Variation with Temperature

25

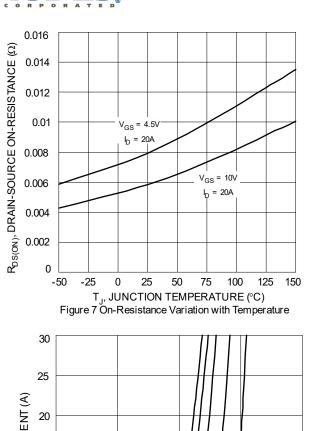
-50

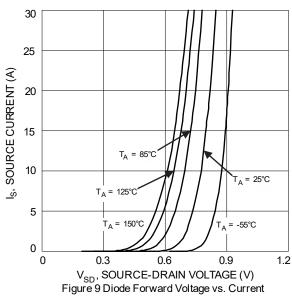
75

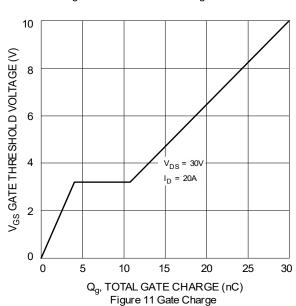
100

125 150









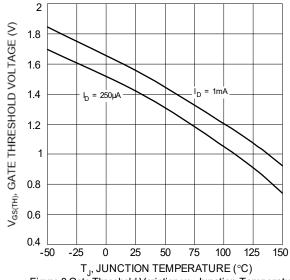
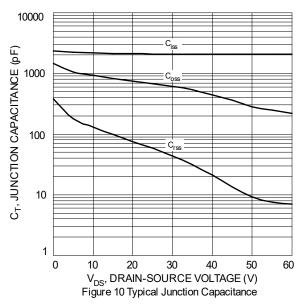
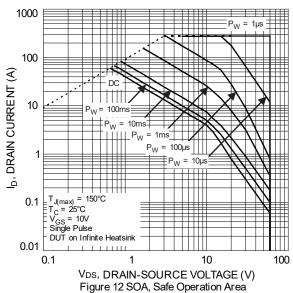
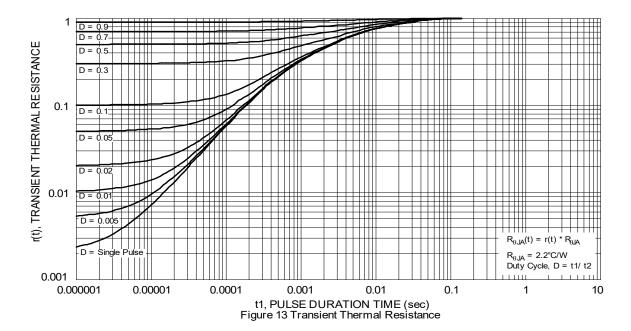


Figure 8 Gate Threshold Variation vs. Junction Temperature









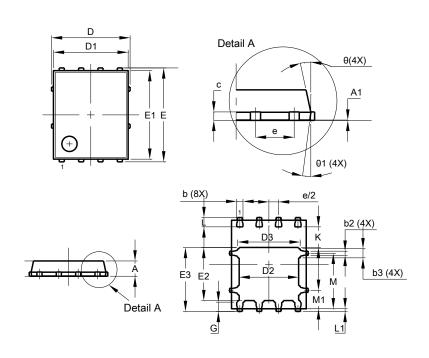


# **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.

Site 1:

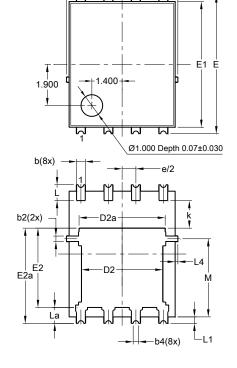
#### PowerDI5060-8

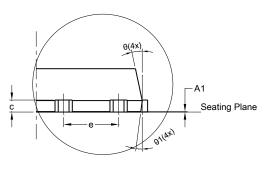


| PowerDI5060-8        |       |          |       |  |
|----------------------|-------|----------|-------|--|
| Dim                  | Min   | Max      | Тур   |  |
| Α                    | 0.90  | 1.10     | 1.00  |  |
| A1                   | 0.00  | 0.05     | -     |  |
| b                    | 0.33  | 0.51     | 0.41  |  |
| b2                   | 0.200 | 0.350    | 0.273 |  |
| b3                   | 0.40  | 0.80     | 0.60  |  |
| C                    | 0.230 | 0.330    | 0.277 |  |
| D                    | ţ     | 5.15 BSC | ;     |  |
| D1                   | 4.70  | 5.10     | 4.90  |  |
| D2                   | 3.70  | 4.10     | 3.90  |  |
| D3                   | 3.90  | 4.30     | 4.10  |  |
| E                    | (     | 3.15 BSC |       |  |
| E1                   | 5.60  | 6.00     | 5.80  |  |
| E2                   | 3.28  | 3.68     | 3.48  |  |
| E3                   | 3.99  | 4.39     | 4.19  |  |
| е                    |       | 1.27 BSC | ;     |  |
| G                    | 0.51  | 0.71     | 0.61  |  |
| K                    | 0.51  | -        | -     |  |
| ٦                    | 0.51  | 0.71     | 0.61  |  |
| L1                   | 0.100 | 0.200    | 0.175 |  |
| М                    | 3.235 | 4.035    | 3.635 |  |
| M1                   | 1.00  | 1.40     | 1.21  |  |
| Θ                    | 10°   | 12°      | 11°   |  |
| Θ1                   | 6°    | 8°       | 7°    |  |
| All Dimensions in mm |       |          |       |  |

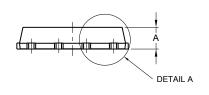
Site 2:

### PowerDI5060-8/SWP (Type UX)





DETAIL A



| PowerDI5060-8/SWP<br>(Type UX) |          |         |       |
|--------------------------------|----------|---------|-------|
| Dim                            | Min      | Max     | Тур   |
| Α                              | 0.90     | 1.10    | 1.00  |
| A1                             | 0        | 0.05    | -     |
| b                              | 0.30     | 0.50    | 0.41  |
| b2                             | 0.20     | 0.35    | 0.25  |
| b4                             | C        | ).25REF | -     |
| С                              | 0.230    | 0.330   | 0.277 |
| D                              | 5        |         | )     |
| D1                             | 4.70     | 5.10    | 4.90  |
| D2                             | 3.56     | 3.96    | 3.76  |
| D2a                            | 3.78     | 4.18    | 3.98  |
| Е                              | 6        | .40 BS0 | )     |
| E1                             | 5.60     | 6.00    | 5.80  |
| E2                             | 3.46     | 3.86    | 3.66  |
| E2a                            | 4.195    | 4.595   | 4.395 |
| е                              | 1        | .27BSC  | )     |
| k                              | 1.05     |         |       |
| L                              | 0.635    | 0.835   | 0.735 |
| La                             | 0.635    | 0.835   | 0.735 |
| L1                             | 0.200    | 0.400   | 0.300 |
| L1a                            | 0.050REF |         |       |
| L4                             | 0.025    | 0.225   | 0.125 |
| М                              | 3.205    | 4.005   | 3.605 |
| θ                              | 10°      | 12°     | 11°   |
| θ1                             | 6°       | 8°      | 7°    |
| All Dimensions in mm           |          |         |       |
|                                |          |         |       |

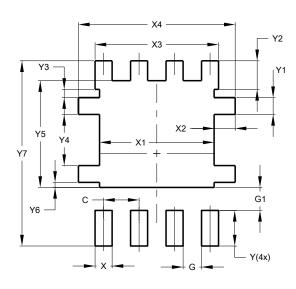


# **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.

Site 1:

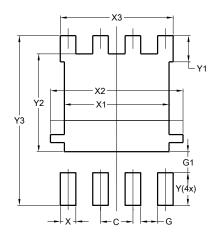
### PowerDI5060-8



| Dimensions | Value (in mm) |
|------------|---------------|
| C          | 1.270         |
| G          | 0.660         |
| G1         | 0.820         |
| Х          | 0.610         |
| X1         | 4.100         |
| X2         | 0.755         |
| Х3         | 4.420         |
| X4         | 5.610         |
| Υ          | 1.270         |
| Y1         | 0.600         |
| Y2         | 1.020         |
| Y3         | 0.295         |
| Y4         | 1.825         |
| Y5         | 3.810         |
| Y6         | 0.180         |
| Y7         | 6.610         |

Site 2:

# PowerDI5060-8/SWP (Type UX)



| Dimensions    | Value   |  |
|---------------|---------|--|
| פווטופווסוווט | (in mm) |  |
| C             | 1.270   |  |
| G             | 0.660   |  |
| G1            | 0.820   |  |
| X             | 0.610   |  |
| X1            | 4.100   |  |
| X2            | 5.190   |  |
| Х3            | 4.420   |  |
| Υ             | 1.270   |  |
| Y1            | 1.020   |  |
| Y2            | 3.810   |  |
| Y3            | 6.610   |  |



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